

## HEXFET® Power MOSFET



Absolute Maximum Ratings
Parameter

P<sub>D</sub> @ T<sub>C</sub> = 25°C Maximum Power Dissipation
Linear Derating Factor

I<sub>D</sub> @ T<sub>C</sub> = 100°C Continuous Drain Current, V<sub>GS</sub> @ 10V (Silicon Limited)

I<sub>D</sub> @ T<sub>C</sub> = 25°C Continuous Drain Current, V<sub>GS</sub> @ 10V (Package Limited

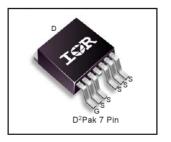
Storage Temperature Range
Soldering Temperature, for 10 seconds

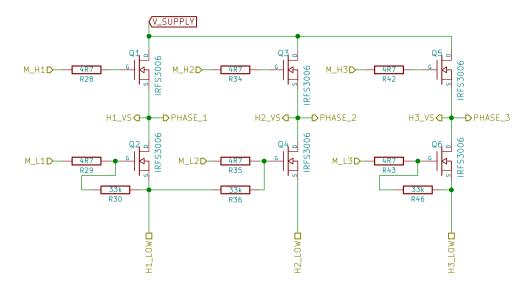
Pulsed Drain Current @

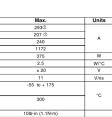
Gate-to-Source Voltage Peak Diode Recovery ®

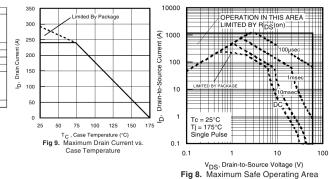
(1.6mm from case) Mounting torque, 6-32 or M3 screw

V <sub>DSS</sub>	60V	
R <sub>DS(on)</sub> typ.	1.5m $\Omega$	
max.	<b>2.1m</b> Ω	
I <sub>D</sub> (Silicon Limited)	293A①	
I <sub>D (Package Limited)</sub>	240A	









Benjamin Vedder

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Title:	BLDC	Driver	4.6
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Size: A4	Date: 25 A	Nug 2014	Rev: 4.6
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